CT3401A-R3

P-Channel Enhancement MOSFET

Features

- Drain-Source Breakdown Voltage V_{DSS} - 30 V
- Drain-Source On-Resistance
  - $R_{DS(ON)}$ 33mΩ, at V_{GS}= - 10V, I_{DS}= - 4.2A
  - $R_{DS(ON)}$ 38mΩ, at V_{GS}= - 4.5V, I_{DS}= - 4.0A
  - $R_{DS(ON)}$ 51mΩ, at V_{GS}= - 2.5V, I_{DS}= - 1.0A
- Continuous Drain Current at T_A=25°C I_D = - 4.2A
- Advanced high cell density Trench Technology
- RoHS Compliance & Halogen Free

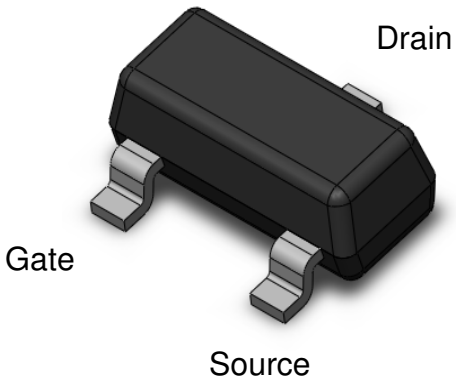
Description

The CT3401A-R3 uses high performance Trench Technology to provide excellent $R_{DS(ON)}$ and low gate charge which is suitable for low voltage application.

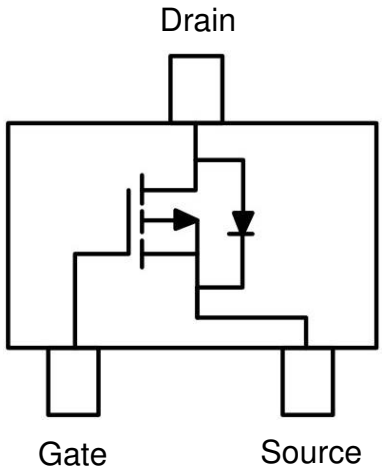
Applications

- Power Management
- LCD Display inverter
- Load Switch

Package Outline



Schematic



Absolute Maximum Rating at 25°C

Symbol	*Parameters*	*Ratings*	*Units*	*Notes*
V_{DS}	Drain-Source Voltage	-30	V	
V_{GS}	Gate-Source Voltage	±12	V	
I_D	Continuous Drain Current	-4.2	A	1
I_{DM}	Pulsed Drain Current	-30	A	1
P_D	Total Power Dissipation	1.4	W	2
T_{STG}	Storage Temperature Range	-55 to 150	°C	
T_J	Operating Junction Temperature Range	-55 to 150	°C	

Thermal Characteristics

Symbol	*Parameters*	*Test Conditions*	*Min*	*Typ*	*Max*	*Units*	*Notes*
$R_{\Theta JA}$	Thermal Resistance Junction-Ambient (t=10s)		-	140	-	°C /W	1,4

Electrical Characteristics T_A = 25℃ (unless otherwise specified)

Static Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
B_{VDSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= - 0.25μA	-30	-	-	V	
I_{DSS}	Drain-Source Leakage Current	V_{DS} = -30V, V_{GS} = 0V	-	-	-1	μA	
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±12V, V_{DS} = 0V	-	-	±100	nA	

On Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$R_{DS(ON)}$	Drain-Source On-Resistance	V_{GS} = -10V, I_D = -4.2A	-	33	50	m	3
		V_{GS} = -4.5V, I_D = -4.0A	-	38	60	mΩ	
		V_{GS} = -2.5V, I_D = -1.0A	-	51	85	mΩ	
$V_{GS(TH)}$	Gate-Source Threshold Voltage	V_{GS} = V_{DS}, I_D = -250μA	-0.47	-	-1.3	V	3

Dynamic Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
C_{ISS}	Input Capacitance	V_{DS} = - 10V , V_{GS} = 0V, f=1MHz	-	1320	-	pF	
C_{OSS}	Output Capacitance		-	88	-		
C_{RSS}	Reverse Transfer Capacitance		-	72	-		

Switching Characteristics

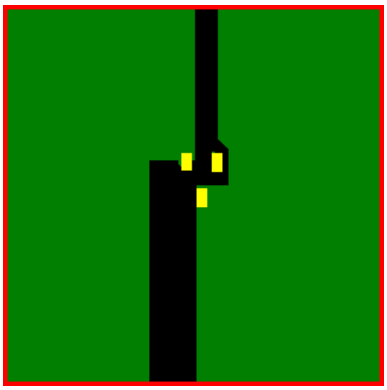
Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$T_{D(ON)}$	Turn-On Delay Time	V_{DS} = -15V , V_{GS} = - 10V, R_G = 3Ω, I_D = -4.2A	-	10.7	-	ns	
T_R	Rise Time		-	11.2	-		
$T_{D(OFF)}$	Turn-Off Delay Time		-	47.1	-		
T_F	Fall Time		-	6.7			
Q_G	Total Gate Charge	V_{DS} = -4.5V , V_{GS} = -105, I_D = -4.2A	-	12.4	-	nC	
Q_{GS}	Gate-Source Charge		-	2.9	-		
Q_{GD}	Gate-Drain (Miller) Charge		-	3.5	-		

Drain-Source Diode Characteristics

Symbol	*Parameters*	*Test Conditions*	*Min*	*Typ*	*Max*	*Units*	*Notes*
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_{SD} = -1.0A			1.2	V	
I_{SD}	Body Diode Continuous Current				-4.2	A	1

Note:

1. The power dissipation is limited by 150℃junction temperature.
2. Device mounted on a glass-epoxy board



FR-4

25.4 × 25.4 mm .

2 Oz Copper

Test Board

3. The data tested by pulsed , pulse width ≦ 300μs , duty cycle ≦ 2%
4. Thermal Resistance follow JESD51-3.

Typical Characteristic Curves

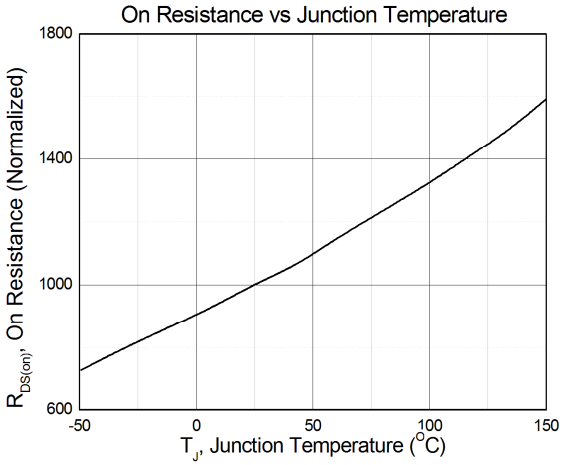


Figure 1

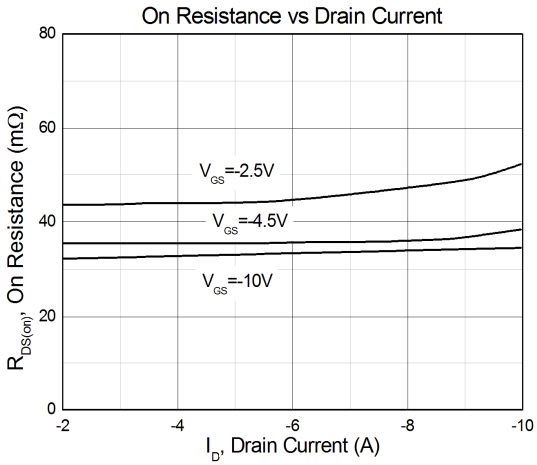


Figure 2

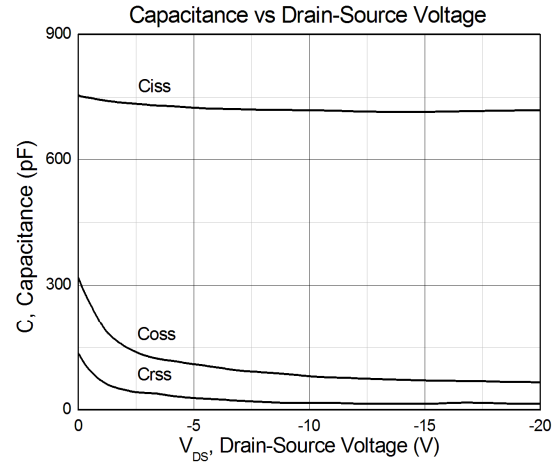


Figure 3

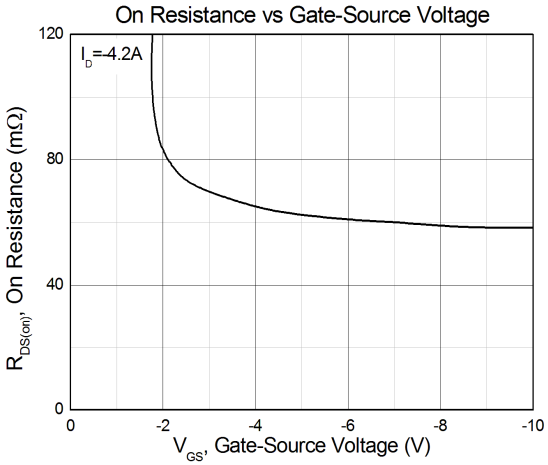


Figure 4

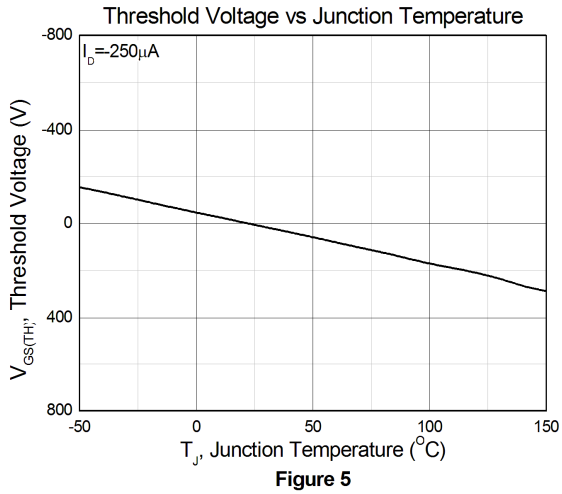


Figure 5

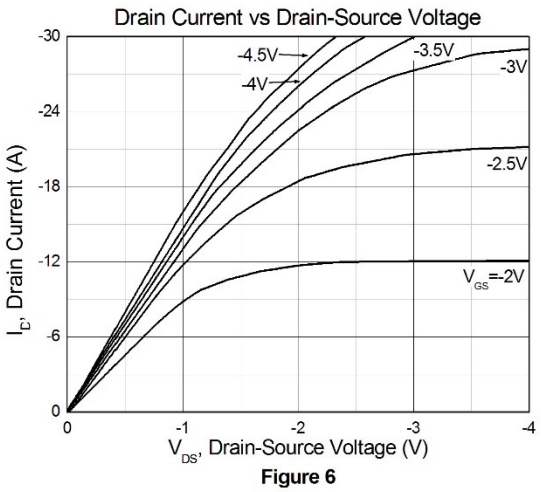


Figure 6

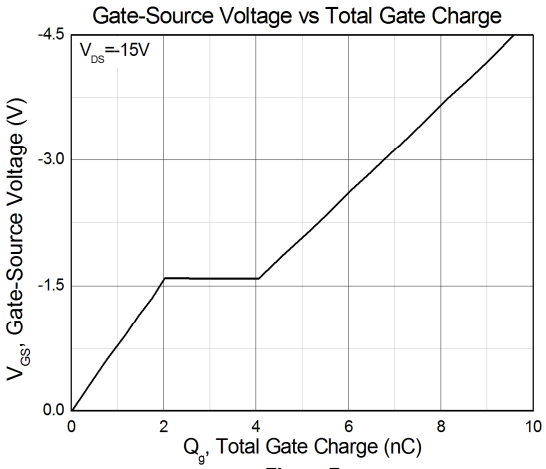


Figure 7

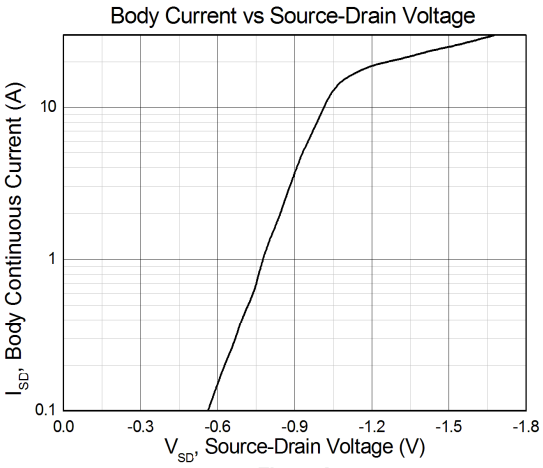


Figure 8

Test Circuits & Waveforms

Figure 9: Gate Charge Test Circuit

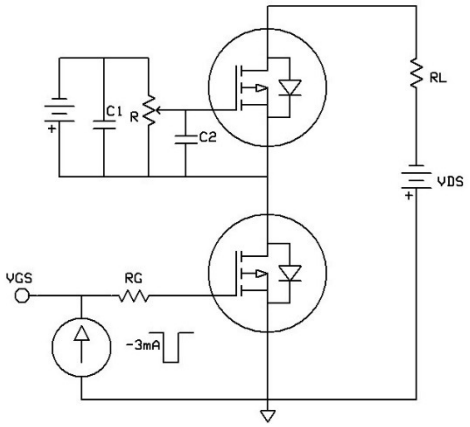


Figure 10: Gate Charge Waveform

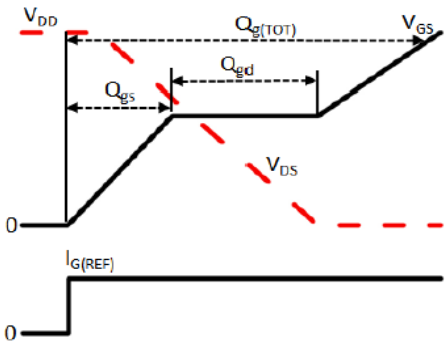


Figure 11: Switching Time Test Circuit

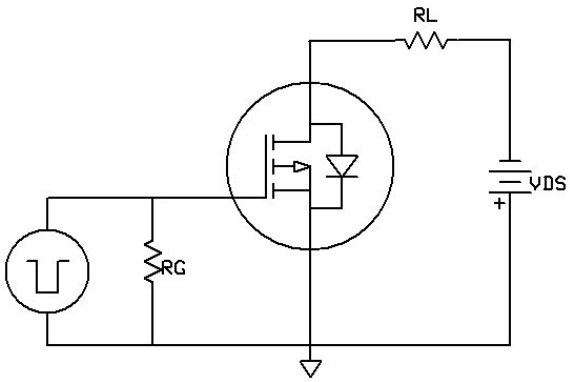
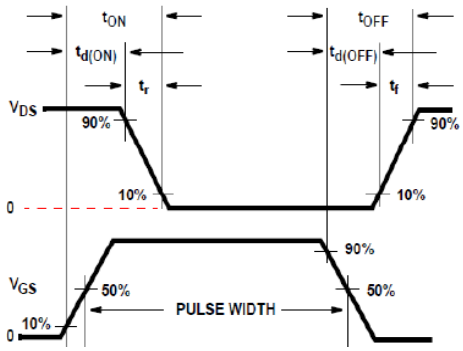
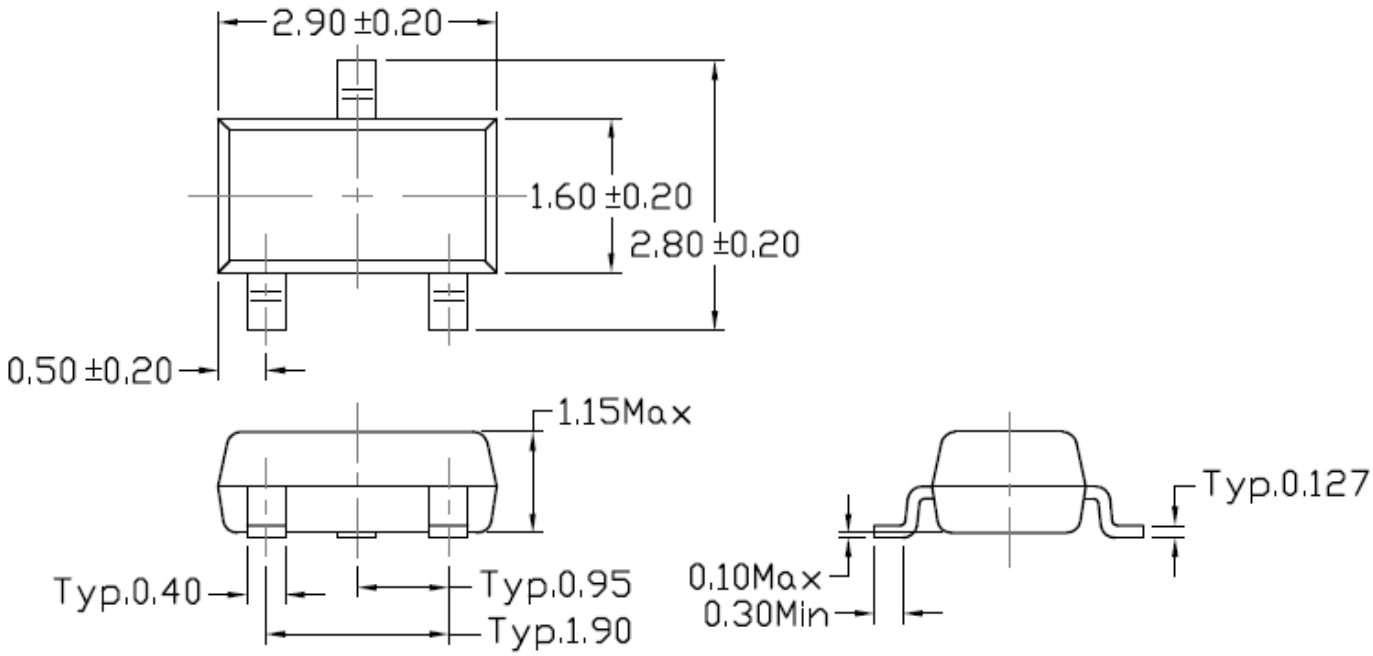


Figure 12: Switching Time Waveform

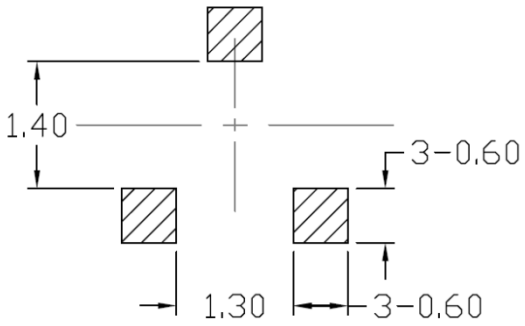


Package Dimension (SC-59)



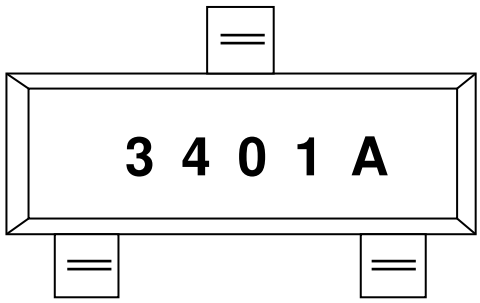
Note: Dimensions in mm

Recommended pad layout for surface mount leadform



Note: Dimensions in mm

Marking Information

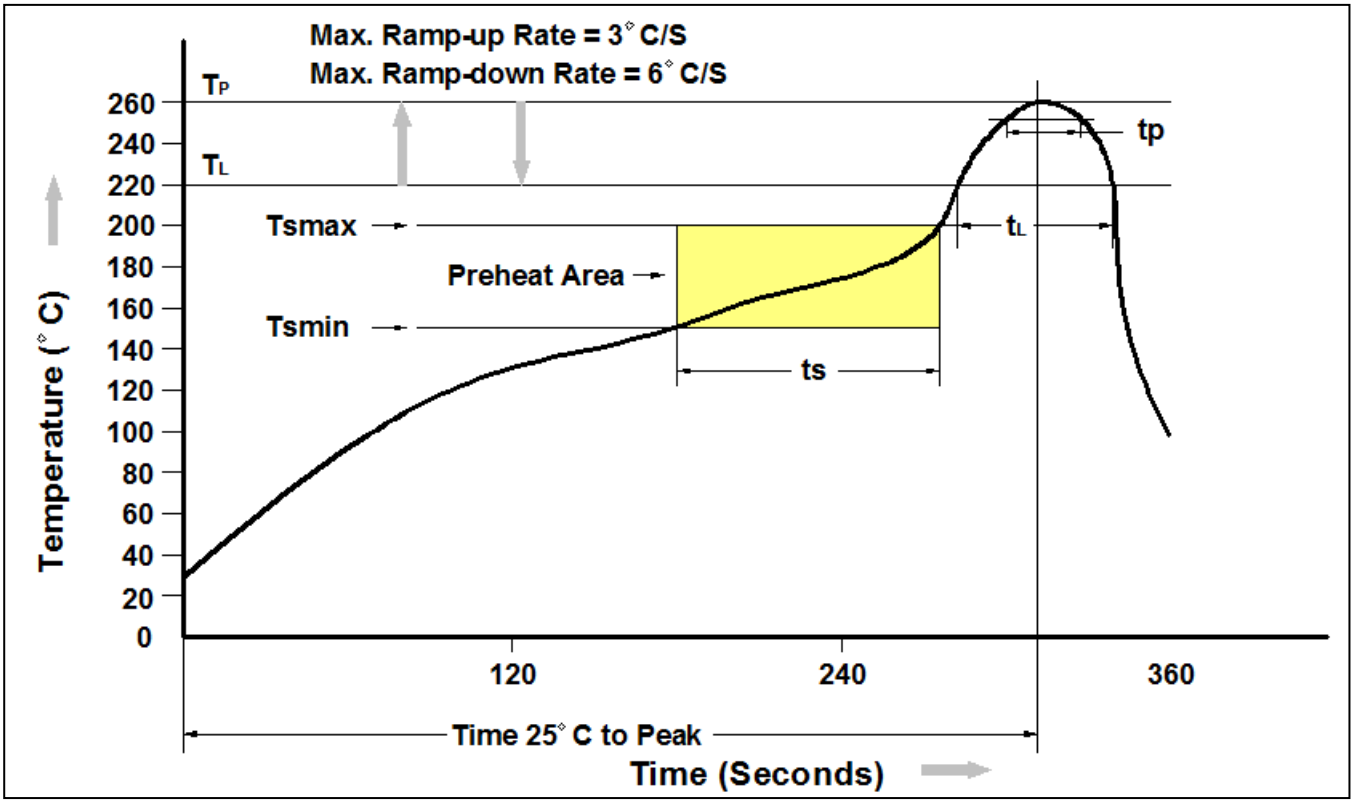


3401A : Device Number

Ordering Information

Part Number	*Description*	*Quantity*
CT3401A-R3	SC-59 Reel	3000 pcs

Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150℃
Temperature Max. (Tsmax)	200℃
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t_L to t_P)	3℃/second max.
Liquidous Temperature (T_L)	217℃
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Body Package Temperature	260℃ +0℃ / -5℃
Time (t_P) within 5℃ of 260℃	30 seconds
Ramp-down Rate (T_P to T_L)	6℃/second max
Time 25℃ to Peak Temperature	8 minutes max.

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